## NLAS5223C, NLAS5223CL

## Ultra-Low $0.35 \Omega$ <br> Dual SPDT Analog Switch

The NLAS5223C is an advanced CMOS analog switch fabricated in Sub-micron silicon gate CMOS technology. The device is a dual Independent Single Pole Double Throw (SPDT) switch featuring Ultra-Low $\mathrm{R}_{\mathrm{ON}}$ of $0.35 \Omega$, at $\mathrm{V}_{\mathrm{CC}}=4.3 \mathrm{~V}$.

The part also features guaranteed Break Before Make (BBM) switching, assuring the switches never short the driver.

## Features

- Ultra-Low $\mathrm{R}_{\mathrm{ON}}, 0.35 \Omega$ (typ) at $\mathrm{V}_{\mathrm{CC}}=4.3 \mathrm{~V}$
- NLAS5223C Interfaces with 2.8 V Chipset
- NLAS5223CL Interfaces with 1.8 V Chipset
- Single Supply Operation from 1.65-4.5 V
- Full 0-V $\mathrm{V}_{\mathrm{CC}}$ Signal Handling Capability
- High Off-Channel Isolation
- Low Standby Current, < 50 nA
- Low Distortion
- $\mathrm{R}_{\mathrm{ON}}$ Flatness of $0.15 \Omega$
- High Continuous Current Capability
- $\pm 320 \mathrm{~mA}$ Through Each Switch
- Large Current Clamping Diodes at Analog Inputs - $\pm 100 \mathrm{~mA}$ Continuous Current Capability
- Package:
- $1.4 \times 1.8 \times 0.55 \mathrm{~mm}$ UQFN10 Pb-Free
- These are $\mathrm{Pb}-$ Free Devices


## Applications

- Cell Phone Audio Block
- Speaker and Earphone Switching
- Ring-Tone Chip/Amplifier Switching
- Modems



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MARKING
DIAGRAM


XX = Specific Device Code
$\overline{\mathrm{M}} \quad=$ Date Code/Assembly Location

- $\quad=$ Pb-Free Device
(Note: Microdot may be in either location)


FUNCTION TABLE

| IN $\mathbf{1 , 2}$ | NO $\mathbf{1 , 2}$ | NC $\mathbf{1 , 2}$ |
| :---: | :---: | :---: |
| 0 | OFF | ON |
| 1 | ON | OFF |

## ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.


Figure 1. Logic Equivalent Circuit

## PIN DESCRIPTION

| QFN PIN \# | Symbol | Name and Function |
| :---: | :---: | :--- |
| $2,5,7,10$ | NC1 to NC2, NO1 to NO2 | Independent Channels |
| 4,8 | IN1 and IN2 | Controls |
| 3,9 | COM1 and COM2 | Common Channels |
| 6 | GND | Ground (V) |
| 1 | $\mathrm{~V}_{\mathrm{CC}}$ | Positive Supply Voltage |

## MAXIMUM RATINGS

| Symbol | Parameter | Value | Unit |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive DC Supply Voltage | -0.5 to +7.0 | V |
| $\mathrm{V}_{\text {IS }}$ | Analog Input Voltage ( $\mathrm{V}_{\mathrm{NO}}, \mathrm{V}_{\mathrm{NC}}$, or $\mathrm{V}_{\mathrm{COM}}$ ) | $-0.5 \leq \mathrm{V}_{\text {IS }} \leq \mathrm{V}_{\text {CC }}+0.5$ | V |
| $\mathrm{V}_{\mathrm{IN}}$ | Digital Select Input Voltage | $-0.5 \leq \mathrm{V}_{\text {IN }} \leq+5.5$ | V |
| $l_{\text {anl1 }}$ | Continuous DC Current from COM to NC/NO | $\pm 320$ | mA |
| lanl-pk1 | Peak Current from COM to NC/NO, 10\% Duty Cycle, $100 \mathrm{~ms}=\mathrm{t}_{\text {ON }}$ (Note 1) | $\pm 600$ | mA |
| $l_{\text {anl-pk2 }}$ | Instantaneous Peak Current from COM to NC/NO, 10\% Duty Cycle, ton < 1 us | $\pm 850$ | mA |
| IClmp | Continuous DC Current into COM/NO/NC with Respect to V ${ }_{\text {CC }}$ or GND | $\pm 100$ | mA |
| ESD | ESD Withstand Voltage Human Body Model (HBM) | >3000 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Defined as $10 \%$ ON, $90 \%$ OFF Duty Cycle.

## RECOMMENDED OPERATING CONDITIONS

| Symbol | Parameter | Min | Max | Unit |
| :---: | :--- | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | DC Supply Voltage | 1.65 | 4.5 | V |
| $\mathrm{~V}_{\mathrm{IN}}$ | Digital Select Input Voltage (OVT) Overvoltage Tolerance | GND | 4.5 | V |
| $\mathrm{~V}_{\mathrm{IS}}$ | Analog Input Voltage (NC, NO, COM) | GND | $\mathrm{V}_{\mathrm{CC}}$ | V |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range | -40 | +85 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{t}_{\mathrm{r}}, \mathrm{t}_{\mathrm{f}}$ | Input Rise or Fall Time, SELECT |  |  | n |
|  | $\mathrm{V}_{\mathrm{CC}}=1.6 \mathrm{~V}-2.7 \mathrm{~V}$ |  |  |  |
|  | $\mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V}-4.5 \mathrm{~V}$ |  | 20 |  |

[^0] the Recommended Operating Ranges limits may affect device reliability.

NLAS5223C DC CHARACTERISTICS - DIGITAL SECTION (Voltages Referenced to GND)

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ | Guaranteed Limit |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage, Select Inputs |  | $\begin{aligned} & 3.0 \\ & 4.3 \end{aligned}$ | $\begin{aligned} & \hline 1.4 \\ & 2.0 \end{aligned}$ | $\begin{aligned} & 1.4 \\ & 2.0 \end{aligned}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage, Select Inputs |  | $\begin{aligned} & 3.0 \\ & 4.3 \end{aligned}$ | $\begin{aligned} & 0.7 \\ & 0.8 \end{aligned}$ | $\begin{aligned} & 0.7 \\ & 0.8 \end{aligned}$ | V |
| 1 IN | Maximum Input Leakage Current, Select Inputs | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {CC }}$ or GND | 4.3 | $\pm 0.1$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| IOFF | Power Off Leakage Current | $\mathrm{V}_{\text {IN }}=\mathrm{V}_{\text {CC }}$ or GND | 0 | $\pm 0.5$ | $\pm 2.0$ | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\mathrm{CC}}$ | Maximum Quiescent Supply Current (Note 2) | Select and $\mathrm{V}_{\text {IS }}=\mathrm{V}_{\text {CC }}$ or GND | 1.65 to 4.5 | $\pm 1.0$ | $\pm 2.0$ | $\mu \mathrm{A}$ |

2. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

NLAS5223C DC ELECTRICAL CHARACTERISTICS - ANALOG SECTION

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ | Guaranteed Maximum Limit |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ |  | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | Min | Max | Min | Max |  |
| RON | NC/NO On-Resistance (Note 3) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\text {IN }}=\mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{IS}}=\mathrm{GND} \text { to } \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{gathered} 0.4 \\ 0.35 \end{gathered}$ |  | $\begin{aligned} & 0.5 \\ & 0.4 \end{aligned}$ | $\Omega$ |
| $\mathrm{R}_{\text {FLAT }}$ | NC/NO On-Resistance Flatness (Notes 3 and 4) | $\begin{aligned} & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{IS}}=0 \text { to } \mathrm{V}_{\mathrm{CC}} \end{aligned}$ | $\begin{aligned} & 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{aligned} & \hline 0.16 \\ & 0.11 \end{aligned}$ |  | $\begin{aligned} & 0.20 \\ & 0.14 \end{aligned}$ | $\Omega$ |
| $\Delta \mathrm{R}_{\text {ON }}$ | On-Resistance Match Between Channels (Notes 3 and 5) | $\begin{aligned} & \hline \mathrm{V}_{\text {IS }}=1.5 \mathrm{~V} ; \\ & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \\ & \mathrm{~V}_{\text {IS }}=2.2 \mathrm{~V} ; \\ & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & \hline 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{aligned} & 0.05 \\ & 0.05 \end{aligned}$ |  | $\begin{aligned} & 0.05 \\ & 0.05 \end{aligned}$ | $\Omega$ |
| $\mathrm{I}_{\mathrm{NC} \text { (OFF) }}$ $\mathrm{I}_{\mathrm{NO}(\mathrm{OFF})}$ | NC or NO Off Leakage Current (Note 3) | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{COM}}=4.0 \mathrm{~V} \end{aligned}$ | 4.3 | -5.0 | 5.0 | -50 | 50 | nA |
| $\mathrm{I}_{\text {COM (ON) }}$ | COM ON <br> Leakage Current (Note 3) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}}$ <br> $\mathrm{V}_{\mathrm{NO}} 0.3 \mathrm{~V}$ or 4.0 V with <br> $\mathrm{V}_{\mathrm{NC}}$ floating or <br> $\mathrm{V}_{\mathrm{NC}} 0.3 \mathrm{~V}$ or 4.0 V with <br> $\mathrm{V}_{\mathrm{NO}}$ floating <br> $\mathrm{V}_{\mathrm{COM}}=0.3 \mathrm{~V}$ or 4.0 V | 4.3 | -10 | 10 | -100 | 100 | nA |

3. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
4. Flatness is defined as the difference between the maximum and minimum value of On-resistance as measured over the specified analog signal ranges.
5. $\Delta \mathrm{R}_{\mathrm{ON}}=\mathrm{R}_{\mathrm{ON}(\mathrm{MAX})}-\mathrm{R}_{\mathrm{ON}(\mathrm{MIN})}$ between NC1 and NC2 or between NO1 and NO2.

NLAS5223CL DC CHARACTERISTICS - DIGITAL SECTION (Voltages Referenced to GND)

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{Cc}}$ | Guaranteed Limit |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |
| $\mathrm{V}_{\mathrm{IH}}$ | Minimum High-Level Input Voltage, Select Inputs |  | $\begin{aligned} & \hline 3.0 \\ & 4.3 \end{aligned}$ | $\begin{aligned} & 1.3 \\ & 1.6 \end{aligned}$ | $\begin{aligned} & 1.3 \\ & 1.6 \end{aligned}$ | V |
| $\mathrm{V}_{\text {IL }}$ | Maximum Low-Level Input Voltage, Select Inputs |  | $\begin{aligned} & 3.0 \\ & 4.3 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.6 \end{aligned}$ | $\begin{aligned} & 0.5 \\ & 0.6 \end{aligned}$ | V |
| $\mathrm{I}_{\mathrm{N}}$ | Maximum Input Leakage Current, Select Inputs | $\mathrm{V}_{\mathrm{IN}}=4.5 \mathrm{~V}$ or GND | 4.3 | $\pm 0.1$ | $\pm 1.0$ | $\mu \mathrm{A}$ |
| IOFF | Power Off Leakage Current | $\mathrm{V}_{\text {IN }}=4.5 \mathrm{~V}$ or GND | 0 | $\pm 0.5$ | $\pm 2.0$ | $\mu \mathrm{A}$ |
| $I_{\text {cc }}$ | Maximum Quiescent Supply Current | Select and $\mathrm{V}_{\text {IS }}=\mathrm{V}_{\text {CC }}$ or GND | 1.65 to 4.5 | $\pm 1.0$ | $\pm 2.0$ | $\mu \mathrm{A}$ |
| Iccv | Maximum Quiescent Supply Current, Low Voltage Driving (Note 6) | $\begin{aligned} & \mathrm{V}_{\text {IS }}=\mathrm{V}_{\mathrm{CC}} \text { or GND } \\ & \mathrm{V}_{\text {IN }}=1.65 \mathrm{~V} \end{aligned}$ | 4.3 | $\pm 145$ | $\pm 150$ | $\mu \mathrm{A}$ |
|  |  | $\begin{aligned} & V_{I S}=V_{C C} \text { or } G N D \\ & V_{I N}=1.80 \mathrm{~V} \end{aligned}$ |  | $\pm 125$ | $\pm 130$ |  |
|  |  | $\begin{aligned} & V_{I S}=V_{C C} \text { or GND } \\ & V_{I N}=2.60 \mathrm{~V} \end{aligned}$ |  | $\pm 50$ | $\pm 55$ |  |

6. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.

NLAS5223CL DC ELECTRICAL CHARACTERISTICS - ANALOG SECTION

| Symbol | Parameter | Condition | $\mathrm{V}_{\mathrm{cc}}$ | Guaranteed Maximum Limit |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | $25^{\circ} \mathrm{C}$ |  | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  | Min | Max | Min | Max |  |
| R ${ }_{\text {ON }}$ | NC/NO On-Resistance (Note 7) | $\begin{aligned} & \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{I N}=\mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{I S}=G N D \text { to } \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{I}_{\text {COM }}=100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & \hline 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{gathered} \hline 0.4 \\ 0.35 \end{gathered}$ |  | $\begin{aligned} & \hline 0.5 \\ & 0.4 \end{aligned}$ | $\Omega$ |
| $\mathrm{R}_{\text {FLAT }}$ | NC/NO On-Resistance Flatness (Notes 7 and 8) | $\begin{aligned} & \mathrm{I}_{\mathrm{COM}}=100 \mathrm{~mA} \\ & \mathrm{~V}_{\mathrm{IS}}=0 \text { to } \mathrm{V}_{\mathrm{CC}} \end{aligned}$ | $\begin{aligned} & \hline 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{aligned} & 0.16 \\ & 0.11 \end{aligned}$ |  | $\begin{aligned} & 0.20 \\ & 0.14 \end{aligned}$ | $\Omega$ |
| $\Delta \mathrm{R}_{\mathrm{ON}}$ | On-Resistance Match Between Channels (Notes 7 and 9) | $\begin{aligned} & \hline \mathrm{V}_{I S}=1.5 \mathrm{~V} ; \\ & I_{\mathrm{COM}}=100 \mathrm{~mA} \\ & \mathrm{~V}_{I S}=2.2 \mathrm{~V} ; \\ & I_{\text {COM }}=100 \mathrm{~mA} \end{aligned}$ | $\begin{aligned} & \hline 3.0 \\ & 4.3 \end{aligned}$ |  | $\begin{aligned} & 0.05 \\ & 0.05 \end{aligned}$ |  | $\begin{aligned} & 0.05 \\ & 0.05 \end{aligned}$ | $\Omega$ |
| ${ }^{I_{N C}(\text { OFF })}$ $\mathrm{I}_{\mathrm{NO}(\mathrm{OFF})}$ | NC or NO Off Leakage Current (Note 7) | $\begin{aligned} & \hline \mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}} \\ & \mathrm{~V}_{\mathrm{NO}} \text { or } \mathrm{V}_{\mathrm{NC}}=0.3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{COM}}=4.0 \mathrm{~V} \end{aligned}$ | 4.3 | -10 | 10 | -100 | 100 | nA |
| $\mathrm{I}_{\text {Com(ON) }}$ | COM ON <br> Leakage Current (Note 7) | $\mathrm{V}_{\mathrm{IN}}=\mathrm{V}_{\mathrm{IL}} \text { or } \mathrm{V}_{\mathrm{IH}}$ <br> $\mathrm{V}_{\mathrm{NO}} 0.3 \mathrm{~V}$ or 4.0 V with <br> $\mathrm{V}_{\mathrm{NC}}$ floating or <br> $\mathrm{V}_{\mathrm{NC}} 0.3 \mathrm{~V}$ or 4.0 V with <br> $\mathrm{V}_{\mathrm{NO}}$ floating <br> $\mathrm{V}_{\mathrm{COM}}=0.3 \mathrm{~V}$ or 4.0 V | 4.3 | -10 | 10 | -100 | 100 | nA |

7. Guaranteed by design. Resistance measurements do not include test circuit or package resistance.
8. Flatness is defined as the difference between the maximum and minimum value of On-resistance as measured over the specified analog signal ranges.
9. $\Delta \mathrm{R}_{\mathrm{ON}}=\mathrm{R}_{\mathrm{ON}(\text { MAX })}-\mathrm{R}_{\mathrm{ON}(\text { MIN })}$ between NC1 and NC2 or between NO1 and NO2.

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AC ELECTRICAL CHARACTERISTICS ( $\operatorname{lnput} \mathrm{t}_{\mathrm{r}}=\mathrm{t}_{\mathrm{f}}=3.0 \mathrm{~ns}$ )

| Symbol | Parameter | Test Conditions | $\mathrm{V}_{\mathrm{cc}}$ <br> (V) | $V_{\text {IS }}$ <br> (V) | Guaranteed Maximum Limit |  |  |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  |  | $25^{\circ} \mathrm{C}$ |  |  | $-40^{\circ} \mathrm{C}$ to $+85^{\circ} \mathrm{C}$ |  |  |
|  |  |  |  |  | Min | Typ* | Max | Min | Max |  |
| ton | Turn-On Time | $R_{L}=50 \Omega, C_{L}=35 \mathrm{pF}$ <br> (Figures 3 and 4) | 2.3-4.5 | 1.5 |  |  | 50 |  | 60 | ns |
| toff | Turn-Off Time | $\mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF}$ <br> (Figures 3 and 4) | 2.3-4.5 | 1.5 |  |  | 30 |  | 40 | ns |
| $\mathrm{t}_{\text {BBM }}$ | Minimum Break-Before-Make Time | $\begin{aligned} & \mathrm{V}_{\mathrm{IS}}=3.0 \\ & \mathrm{R}_{\mathrm{L}}=50 \Omega, \mathrm{C}_{\mathrm{L}}=35 \mathrm{pF} \\ & \text { (Figure 2) } \end{aligned}$ | 3.0 | 1.5 | 2 | 15 |  |  |  | ns |


| Typical @ 25, $\mathbf{V}_{\mathbf{C C}}=\mathbf{3 . 6} \mathbf{V}$ |  |  |  |
| :---: | :--- | :---: | :---: |
| $\mathrm{C}_{\mathrm{IN}}$ | Control Pin Input Capacitance | 3.5 | pF |
| $\mathrm{C}_{\mathrm{NO} / \mathrm{NC}}$ | NO, NC Port Capacitance | 60 | pF |
| $\mathrm{C}_{\mathrm{COM}}$ | COM Port Capacitance When Switch is Enabled | 200 | pF |

${ }^{*}$ Typical Characteristics are at $25^{\circ} \mathrm{C}$.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

| Symbol | Parameter | Condition | $\begin{aligned} & V_{c c} \\ & (\mathrm{~V}) \end{aligned}$ | $25^{\circ} \mathrm{C}$ | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  |  |  |  | Typical |  |
| BW | Maximum On-Channel -3 dB Bandwidth or Minimum Frequency Response | $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND <br> (Figure 5) | 1.65-4.5 | 24 | MHz |
| $\mathrm{V}_{\text {ONL }}$ | Maximum Feed-through On Loss | $\mathrm{V}_{\mathrm{IN}}=0 \mathrm{dBm}$ @ 100 kHz to 50 MHz <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 5) | 1.65-4.5 | -0.06 | dB |
| VISO | Off-Channel Isolation | $\mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{IS}}=1 \mathrm{VRMS} ; \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF}$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 5) | 1.65-4.5 | -68 | dB |
| Q | Charge Injection Select Input to Common I/O | $\begin{aligned} & \mathrm{V}_{\text {IN }}=V_{\text {CC to }} \text { GND, } R_{\text {IS }}=0 \Omega, C_{\mathrm{L}}=1.0 \mathrm{nF} \\ & \mathrm{Q}=\mathrm{C}_{\mathrm{L}} \times \mathrm{DV}_{\text {OUT }} \text { (Figure 6) } \end{aligned}$ | 1.65-4.5 | 38 | pC |
| THD | Total Harmonic Distortion THD + Noise | $\begin{aligned} & \mathrm{F}_{\text {IS }}=20 \mathrm{~Hz} \text { to } 20 \mathrm{kHz}, \mathrm{R}_{\mathrm{L}}=\mathrm{R}_{\text {gen }}=600 \Omega, \mathrm{C}_{\mathrm{L}}=50 \mathrm{pF} \\ & \mathrm{~V}_{\text {IS }}=2.0 \mathrm{~V} \text { RMS } \end{aligned}$ | 3.0 | 0.08 | \% |
| VCT | Channel-to-Channel Crosstalk | $\mathrm{f}=100 \mathrm{kHz} ; \mathrm{V}_{\mathrm{IS}}=1.0 \mathrm{~V} \text { RMS, } \mathrm{C}_{\mathrm{L}}=5.0 \mathrm{pF}, \mathrm{R}_{\mathrm{L}}=50 \Omega$ <br> $\mathrm{V}_{\text {IN }}$ centered between $\mathrm{V}_{\mathrm{CC}}$ and GND (Figure 5) | 1.65-4.5 | -70 | dB |

10. Off-Channel Isolation $=20 \log 10\left(\mathrm{~V}_{\mathrm{COM}} / \mathrm{V}_{\mathrm{NO}}\right), \mathrm{V}_{\mathrm{COM}}=$ output, $\mathrm{V}_{\mathrm{NO}}=$ input to off switch.

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Figure 2. $\mathrm{t}_{\mathrm{BBM}}$ (Time Break-Before-Make)


Figure 3. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$


Figure 4. $\mathrm{t}_{\mathrm{ON}} / \mathrm{t}_{\mathrm{OFF}}$

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Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. $\mathrm{V}_{\text {ISO }}$, Bandwidth and $\mathrm{V}_{\text {ONL }}$ are independent of the input signal direction.
$\mathrm{V}_{\text {ISO }}=$ Off Channel Isolation $=20 \log \left(\frac{\mathrm{~V}_{\mathrm{OUT}}}{\mathrm{V}_{\text {IN }}}\right)$ for $\mathrm{V}_{\text {IN }}$ at 100 kHz
$\mathrm{V}_{\text {ONL }}=$ On Channel Loss $=20 \log \left(\frac{\mathrm{~V}_{\mathrm{OUT}}}{\mathrm{V}_{\mathrm{IN}}}\right)$ for $\mathrm{V}_{\mathrm{IN}}$ at 100 kHz to 50 MHz
Bandwidth (BW) = the frequency 3 dB below $\mathrm{V}_{\mathrm{ONL}}$
$\mathrm{V}_{\mathrm{CT}}=$ Use $\mathrm{V}_{\text {ISO }}$ setup and test to all other switch analog input/outputs terminated with $50 \Omega$

Figure 5. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V ${ }_{\text {ONL }}$


Figure 6. Charge Injection: (Q)

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Figure 7. Cross Talk vs. Frequency $\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}\right)$


Figure 9. Total Harmonic Distortion

$$
\left(\mathrm{V}_{\mathrm{cc}}=3.0 \mathrm{~V}\right)
$$



Figure 11. On-Resistance vs. Input Voltage $@ 25^{\circ} \mathrm{C}$ and $\mathrm{V}_{\mathrm{cc}}=3.0 \mathrm{~V}$ and 4.3 V


Figure 8. Bandwidth
( $\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}$ )


Figure 10. Off Isolation
$\left(\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}\right)$


Figure 12. On-Resistance vs. Input Voltage $@ \mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$

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Figure 13. On-Resistance vs. Input Voltage
$@ \mathrm{~V}_{\mathrm{CC}}=3.0 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=-40^{\circ} \mathrm{C}$ to $85^{\circ} \mathrm{C}$

## ORDERING INFORMATION

| Device | Marking | Package | Shipping $^{\dagger}$ |
| :--- | :---: | :---: | :---: |
| NLAS5223CMUTAG | AK | UQFN10 <br> (Pb-Free) | $3000 /$ Tape \& Reel |
| NLAS5223CLMUTAG | AU | UQFN10 <br> (Pb-Free) | $3000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.


UQFN10 1.4x1.8, 0.4P
CASE 488AT-01
ISSUE A
DATE 01 AUG 2007
SCALE 5:1


BOTTOM VIEW

MOUNTING FOOTPRINT


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b APPLIES TO PLATED TERMINAL AIMENSION b APPLIES TO PLATED TERMINAL
ANEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

| DIM | MILLIMETERS |  |
| :---: | :---: | :---: |
|  | MIN | MAX |
| A | 0.45 | 0.60 |
| A1 | 0.00 | 0.05 |
| A3 | 0.127 REF |  |
| b | 0.15 |  |
| D | 1.40 .25 |  |
| E | 1.80 BSC |  |
| e | $0.40 ~ B S C ~$ |  |
| L | 0.30 | 0.50 |
| L1 | 0.00 | 0.15 |
| L3 | 0.40 | 0.60 |

GENERIC MARKING DIAGRAM*


$$
\begin{array}{ll}
\text { XX } & =\text { Specific Device Code } \\
\text { M } & =\text { Date Code } \\
\text { - } & =\text { Pb-Free Package }
\end{array}
$$

(Note: Microdot may be in either location)
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-$ Free indicator, "G" or microdot " P ", may or may not be present.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | 10 PIN UQFN, 1.4 X 1.8, 0.4P | PAGE 1 OF 1 |

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